

ULB4132-VB Datasheet N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0. 003				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0. 004				
I _D (A)	120				
Configuration	Single				

FEATURES

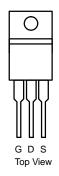
- Trench Power MOSFET
 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU

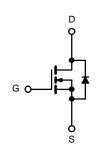


APPLICATIONS

- OR-ing
- Server
- DC/DC







N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C		120	A	
	T _C = 70 °C		60 ^e		
	T _A = 25 °C	I _D	28.8 ^{b, c}		
	T _A = 70 °C		19 ^{b, c}		
Pulsed Drain Current		I _{DM}	380		
Avalanche Current Pulse	L = 0.1 mH	I _{AS}	36		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	64.8	V	
Ocaliana Carres Brain Binda Ocarres	T _C = 25 °C	I-	90 ^{a, e}	Λ	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	3.13 ^{b, c}	Α	
Maximum Power Dissipation	T _C = 25 °C		250 ^a		
	T _C = 70 °C	В	175	w	
	T _A = 25 °C	P _D	3.75 ^{b, c}		
	T _A = 70 °C		2.63 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R _{thJA}	32	40	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6		

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.

- d. 1 = 10 sec.
 d. Maximum under steady state conditions is 90 °C/W.
 e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

服务热线:400-655-8788



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				<u>'</u>		•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 250 A		35		>//00	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \mu A$		- 7.5		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA	
Zana Oata Valtana Basis Oursest		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α	
		$V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		0.003			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 27 \text{ A}$	0.0			Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 28.8 A		160		S	
Dynamic ^b				•			
Input Capacitance	C _{iss}			3100		pF	
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		725			
Reverse Transfer Capacitance	C _{rss}			370			
Total Gate Charge $Q_{g} = V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 28.8 \text{ M}$	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		171	257			
			81.5	123	200		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 28.8 \text{ A}$		34		nC	
Gate-Drain Charge	Q_{gd}			29			
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω	
Turn-On Delay Time	t _{d(on)}			18	27		
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.625 Ω		11	17		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 24 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		70	105		
Fall Time	t _f			10	15	1	
Turn-On Delay Time	t _{d(on)}			55	83	ns -	
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.67 Ω		180	270		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 22.5$ A, $V_{GEN}=4.5$ V, $R_g=1$ Ω		55	83		
Fall Time	t _f			12	18	1	
Drain-Source Body Diode Characteristic	cs						
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			90	۸	
Pulse Diode Forward Current ^a	I _{SM}				90	A	
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	L_ = 20 A di/dt = 100 A/vo T = 25 °C		70.2	105	nC	
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		27			
Reverse Recovery Rise Time	t _b	7		25		ns	

Notes:

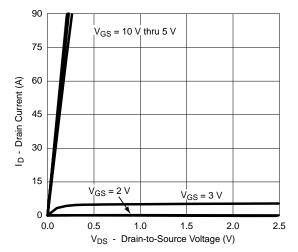
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

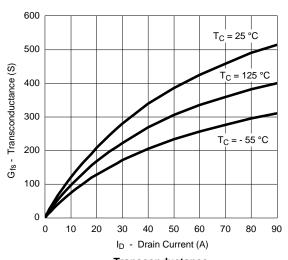
服务热线:400-655-8788



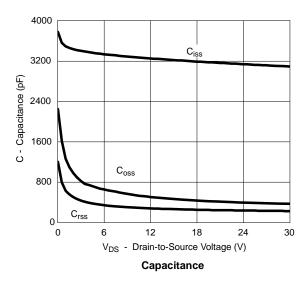
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

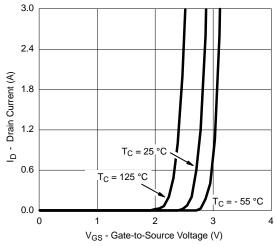


Output Characteristics

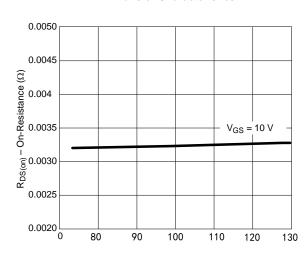


Transconductance

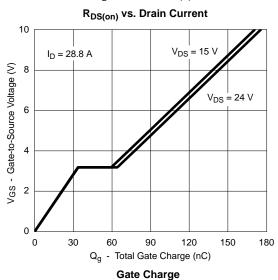




Transfer Characteristics



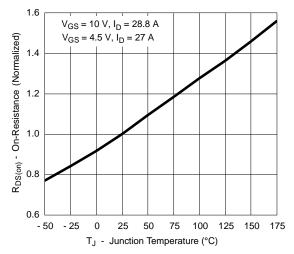
I_D - Drain Current (A)



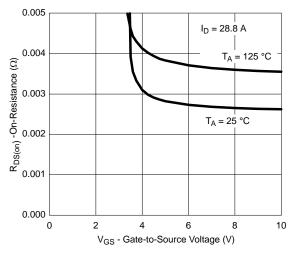
服务热线:400-655-8788



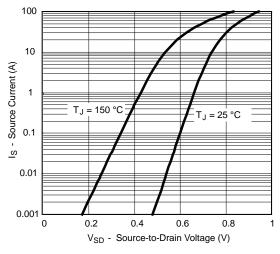
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



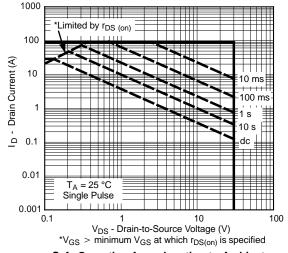
 $R_{DS(on)}$ vs. V_{GS} vs. Temperature



Forward Diode Voltage vs. Temperature



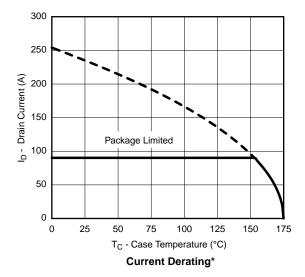
Threshold Voltage

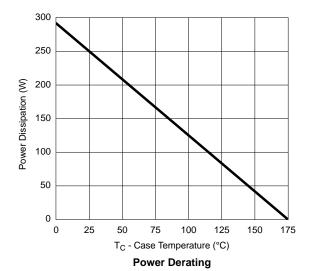


Safe Operating Area, Junction-to-Ambient

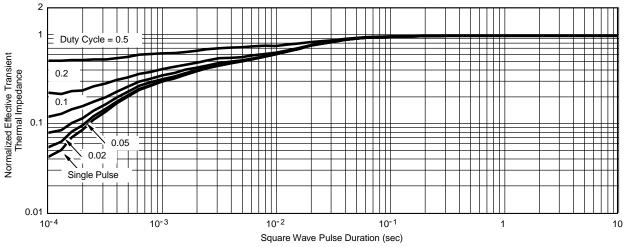


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





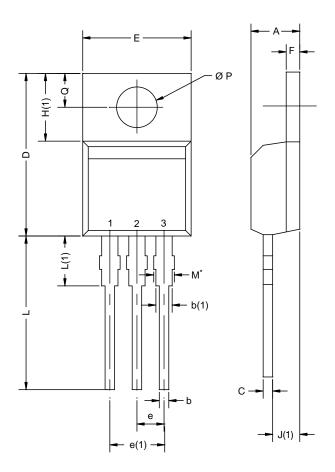
*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case



TO-220AB



	MILLIM	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
E	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

Notes

 $^{^{\}star}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



Disclaimer

All products due to improve reliability, function or design or for other reasons, product specifications and data are subject to change without notice.

Taiwan VBsemi Electronics Co., Ltd., branches, agents, employees, and all persons acting on its or their representatives (collectively, the "Taiwan VBsemi"), assumes no responsibility for any errors, inaccuracies or incomplete data contained in the table or any other any disclosure of any information related to the product.(www.VBsemi.com)

Taiwan VBsemi makes no guarantee, representation or warranty on the product for any particular purpose of any goods or continuous production. To the maximum extent permitted by applicable law on Taiwan VBsemi relinquished: (1) any application and all liability arising out of or use of any products; (2) any and all liability, including but not limited to special, consequential damages or incidental; (3) any and all implied warranties, including a particular purpose, non-infringement and merchantability guarantee.

Statement on certain types of applications are based on knowledge of the product is often used in a typical application of the general product VBsemi Taiwan demand that the Taiwan VBsemi of. Statement on whether the product is suitable for a particular application is non-binding. It is the customer's responsibility to verify specific product features in the products described in the specification is appropriate for use in a particular application. Parameter data sheets and technical specifications can be provided may vary depending on the application and performance over time. All operating parameters, including typical parameters must be made by customer's technical experts validated for each customer application. Product specifications do not expand or modify Taiwan VBsemi purchasing terms and conditions, including but not limited to warranty herein.

Unless expressly stated in writing, Taiwan VBsemi products are not intended for use in medical, life saving, or life sustaining applications or any other application. Wherein VBsemi product failure could lead to personal injury or death, use or sale of products used in Taiwan VBsemi such applications using client did not express their own risk. Contact your authorized Taiwan VBsemi people who are related to product design applications and other terms and conditions in writing.

The information provided in this document and the company's products without a license, express or implied, by estoppel or otherwise, to any intellectual property rights granted to the VBsemi act or document. Product names and trademarks referred to herein are trademarks of their respective representatives will be all.

Material Category Policy

Taiwan VBsemi Electronics Co., Ltd., hereby certify that all of the products are determined to be RoHS compliant and meets the definition of restrictions under Directive of the European Parliament 2011/65 / EU, 2011 Nian. 6. 8 Ri Yue restrict the use of certain hazardous substances in electrical and electronic equipment (EEE) - modification, unless otherwise specified as inconsistent.(www.VBsemi.com)

Please note that some documents may still refer to Taiwan VBsemi RoHS Directive 2002/95 / EC. We confirm that all products identified as consistent with the Directive 2002/95 / EC European Directive 2011/65 /.

Taiwan VBsemi Electronics Co., Ltd. hereby certify that all of its products comply identified as halogen-free halogen-free standards required by the JEDEC JS709A. Please note that some Taiwanese VBsemi documents still refer to the definition of IEC 61249-2-21, and we are sure that all products conform to confirm compliance with IEC 61249-2-21 standard level JS709A.